

GM4672

NPN EPITAXIAL SILICON TRANSISTOR

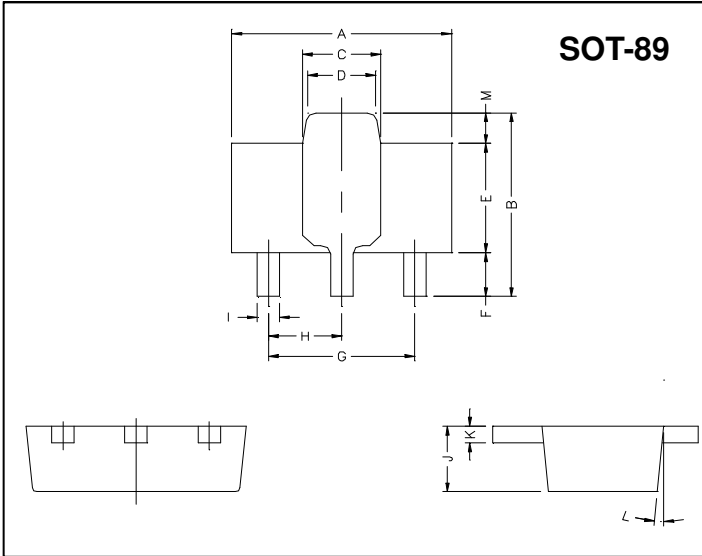
Description

The GM4672 is designed for low frequency amplifier applications.

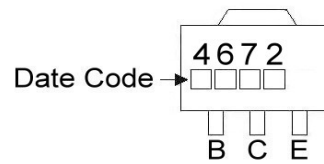
Features

- Low saturation voltage, typically $V_{CE(sat)} = 0.1V$ at $I_C/I_B = 1A/50mA$
- Excellent DC current gain characteristics

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings (TA=25°C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	2	A
Collector Current (Pulse PW=10ms)	I_C	5	A
Total Device Dissipation	P_D	2	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 ~ +150	°C

Electrical Characteristics (TA = 25°C unless otherwise noted)

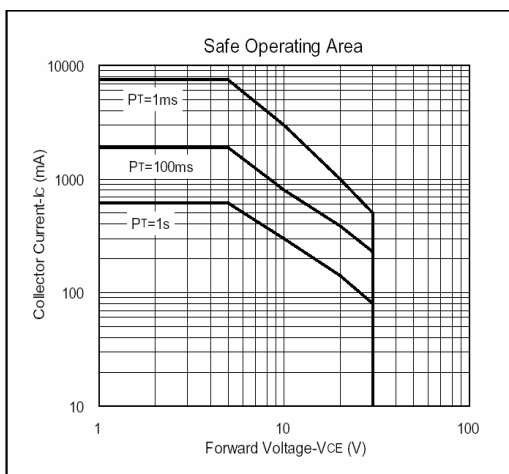
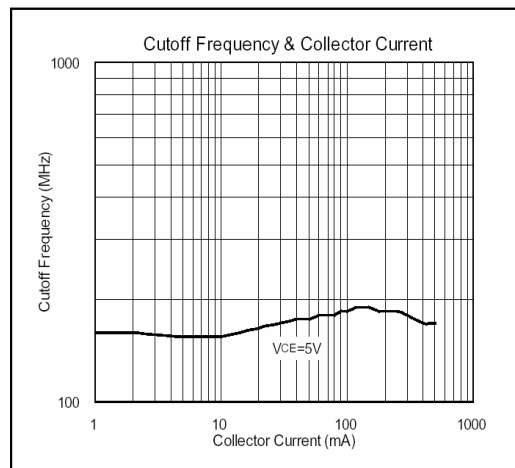
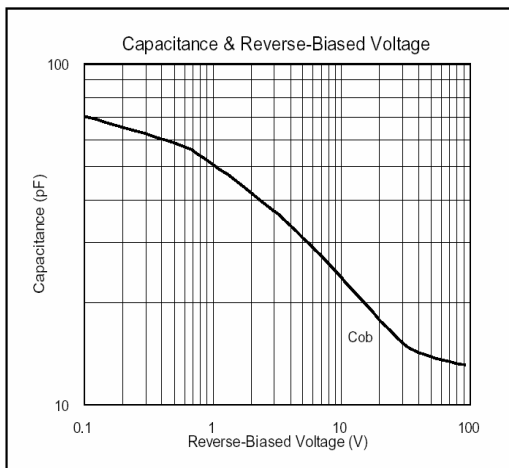
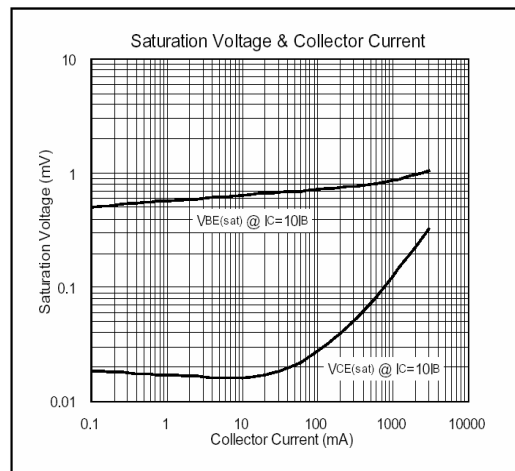
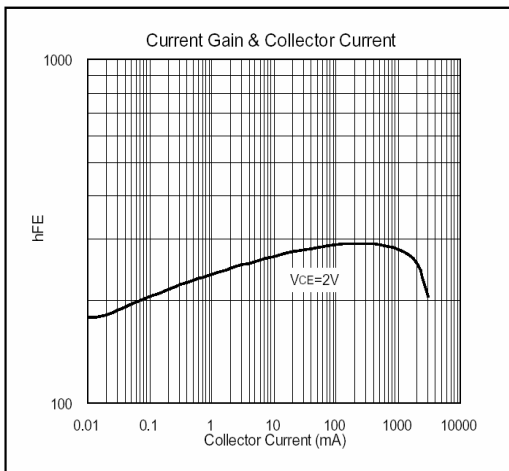
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V_{CBO}	60	-	-	V	$I_C = 50\mu A, I_E = 0$
V_{CEO}	50	-	-	V	$I_C = 1mA, I_B = 0$
V_{EBO}	6	-	-	V	$I_E = 50\mu A, I_C = 0$
I_{CBO}	-	-	100	nA	$V_{CB} = 60V, I_E = 0$
I_{EBO}	-	-	100	nA	$V_{EB} = 5V, I_C = 0$
* $V_{CE(sat)}$	-	0.1	0.35	V	$I_C = 1A, I_B = 50mA$
* h_{FE}	120	-	400		$V_{CE} = 2V, I_C = 500mA$
fT	-	210	-	MHz	$V_{CE} = 2V, I_E = 500mA, f = 100MHz$
Cob	-	25	-	pF	$V_{CB} = 10V, I_E = 0, f = 1MHz$

*Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Classification Of h_{FE}

Rank	A	B
Range	120 ~ 240	200 ~ 400

Characteristics Curve



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